



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Gate up to 2kV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



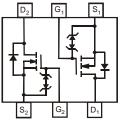


**SOT563** 

Top View



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Top View Internal Schematic

#### Ordering Information (Note 3)

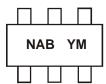
Part Number	Case	Packaging
DMN2004VK-7	SOT563	3000/Tape & Reel
DMN2004VK-13	SOT563	10000/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



 $\begin{array}{l} \mathsf{NAB} = \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{T} = 2006) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$ 

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Т	U	V	W	Х	Y	Z	А	В	С	D	E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

	Characteristic	Symbol	Value	Units	
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Drain Current (Note 4)	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$	ID	540 390	mA
Pulsed Drain Current (10µs pulse,	duty cycle = 1%)	I <sub>DM</sub>	1.5	A	

## **Thermal Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

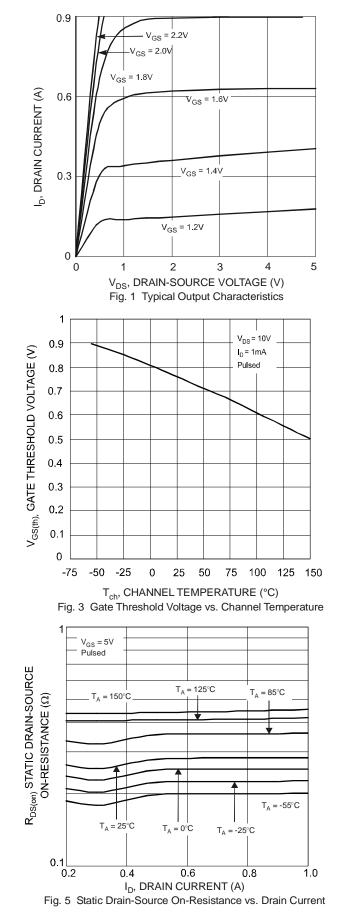
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	PD	250	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	500	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

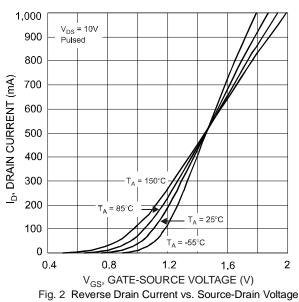
### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μΑ	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1	μΑ	$V_{GS} = \pm 4.5 V$ , $V_{DS} = 0 V$
ON CHARACTERISTICS (Note 5)			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	0.5	0.70 0.9	Ω	$V_{GS} = 2.5V, I_D = 500mA$
			0.7			$V_{GS} = 1.8V, I_D = 350mA$
Forward Transfer Admittance	Y <sub>fs</sub>	200		_	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V <sub>SD</sub>	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 6)			•			
Input Capacitance	Ciss	_		150	pF	
Output Capacitance	C <sub>oss</sub>	_		25	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_		20	pF	
SWITCHING CHARACTERISTICS (Note 6)						
Turn-On Delay Time	t <sub>d(on)</sub>	_	8.0	_	ns	V 40V D 470
Rise Time	tr	_	13.3		ns	$V_{DD} = 10V, R_L = 47\Omega,$
Turn-Off Delay Time	t <sub>d(off)</sub>	_	53.5	_	ns	$I_D = 200$ mA. $V_{GEN} = 4.5$ V,
Fall Time	tf	_	36.1		ns	$-R_{G} = 10\Omega$

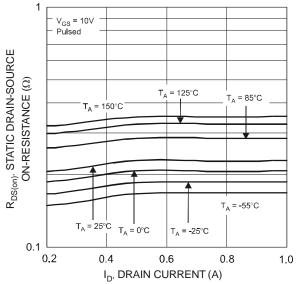
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



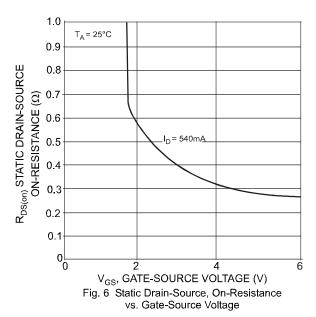






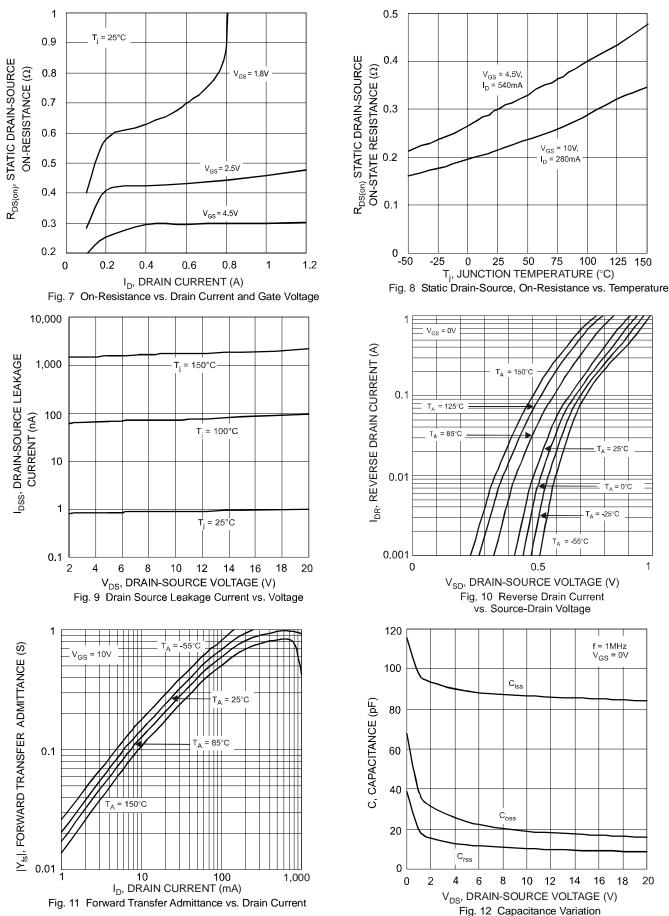






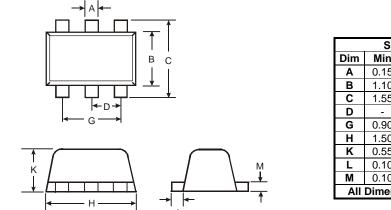






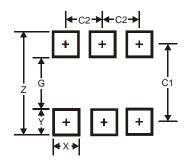


# Package Outline Dimensions



SOT563					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
в	1.10	1.25	1.20		
с	1.55	1.70	1.60		
D	-	-	0.50		
G	0.90	1.10	1.00		
Н	<b>H</b> 1.50 1.70 1.60				
Κ	<b>K</b> 0.55 0.60 0.60				
L	0.10	0.30	0.20		
М	0.10	0.18	0.11		
All Dimensions in mm					

# Suggested Pad Layout



Dimensions	Value (in mm)			
Z	2.2			
G	1.2			
Х	0.375			
Y	0.5			
C1	1.7			
C2	0.5			



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